

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	semi std or none	
	5.0	Overall Thickness	450.00 +/- 10.00 μ m	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00 μ m	Guaranteed by Process
	7.0	Bow	<60.00 μ m	ADE to ASTM F534, 20%
	8.0	Warp	<60.00 μ m	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{111} off 2.5 degree +/- 0.5 degree	Wafer Vendor
	13.0	Handle Carbon Concentration	< 2 e16 at/cm3	Wafer Vendor
	14.0	Handle Thickness	400.00 +/- 5.00 μ m	ADE, 100%
	15.0	Handle Doping Type	N	Wafer Vendor
	16.0	Handle Dopant	Arsenic	Wafer Vendor
	17.0	Handle Resistivity	<0.005 Ohmcm	Wafer Vendor
	18.0	Backside Finish	Lapped and etched with oxide and lasermark	Wafer Vendor
DeviceSilicon	19.0	Device Growth Method	FZ	Wafer Vendor
	20.0	Device Orientation	{111} off 3.5 degree +/- 0.5 degree	Wafer Vendor
	21.0	Nominal Thickness	50.00 +/- 1.00 μ m	FTIR, 100% 9-Pt (note3)
	22.0	Distance to device silicon edge from wafer edge	<= 3mm	Typical by Process
	23.0	Device Doping Type	N	Wafer Vendor
	24.0	Device Dopant	Phosphorous	Wafer Vendor
	25.0	Device Resistivity	> 5000 Ohm-cm	Wafer Vendor
	26.0	Buried Layer Implant	none	implant vendor
	27.0	Voids	0	Bright Light, 100% (note 2)
	28.0	Scratches	0	Bright Light, 100% (note 2)
	29.0	Haze	none	Bright Light, 100% (note 2)

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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information